N-Channel 80-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

i neat	$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$
ole and	80	$82 @ V_{GS} = 10V$	±5.4
s, ess	80	$115 @ V_{GS} = 4.5V$	±4.6
		DFN2x3-8PP	

PRODUCT SUMMARY

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN2x3-8PP saves board space
- Fast switching speed
- High performance trench technology

		DFN2x3-8PP Top View			D
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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			80	\mathbf{V}		
Gate-Source Voltage			±20	V		
	T _A =25°C		±5.4			
Continuous Drain Current ^a	$T_A=70^{\circ}C$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	A			
Pulsed Drain Current ^b	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	±25	1			
Continuous Source Current (Diode Conduction) ^a		Is	2	A		
D	$T_A=25^{\circ}C$	D	3.5	W		
Power Dissipation ^a	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$] ^w				
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
a	t <= 10 sec	D	35	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	$R_{ heta JA}$	81	°C/W	

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM5480N

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Donomoton	C11	T4 C 3'4'	Limits			TT .4		
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{\mathrm{DS}} = V_{\mathrm{GS}}, I_{\mathrm{D}} = 250\mathrm{uA}$	1					
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA		
Zara Cata Valtaga Drain Current	7	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	η, Δ		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A		
D : G . C . D : A		$V_{GS} = 10 \text{ V}, I_D = 4.6 \text{ A}$			86			
Drain-Source On-Resistance ^A	fDS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 3.9 \text{ A}$			115	mΩ		
Forward Tranconductance ^A	gfs	$V_{DS} = 15 \text{ V}, I_D = 4.6 \text{ A}$		11		S		
Diode Forward Voltage	V _{SD}	$I_S = 2.0 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V		
Dynamic ^b								
Total Gate Charge	Qg	V 20 V V 45 V		3.6		nC		
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 4.6 \text{ A}$		1.8				
Gate-Drain Charge	Q_{gd}	ID = 4.0 A		1.3				
Turn-On Delay Time	t _{d(on)}			9				
Rise Time	$t_{\rm r}$	$V_{\rm DD} = 30 \; V, R_L = 30 \; \Omega \;$, Id = 1 A,		10		C		
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 V$		21		nS		
Fall-Time	tf			8				

Notes

- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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